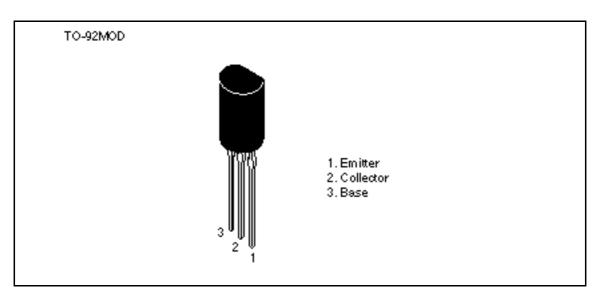
Silicon NPN Epitaxial

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#### Application

- Low frequency power amplifier
- Complementary pair with 2SB562

#### Outline



# **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	25	V
Collector to emitter voltage	V <sub>CEO</sub>	20	V
Emitter to base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>c</sub>	1.0	A
Collector peak current	İ <sub>C(peak)</sub>	1.5	A
Collector power dissipation	P <sub>c</sub>	0.9	W
Junction temperature	Тј	150	°C
Storage temperature	Tstg	–55 to +150	°C



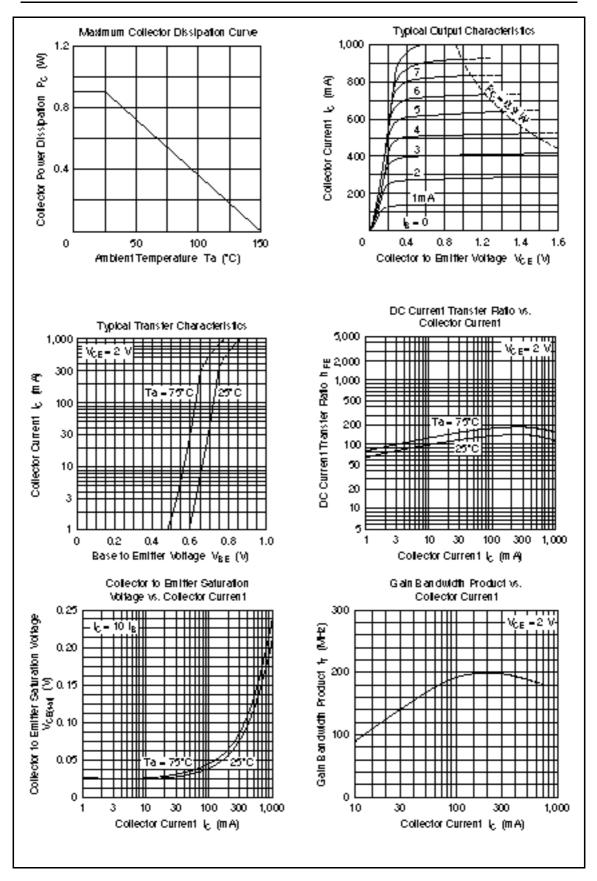
# **Electrical Characteristics** (Ta = $25^{\circ}$ C)

	<u> </u>		-			
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	20	_	_	V	$I_c = 1 \text{ mA}, \text{ R}_{\text{BE}} =$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	5	_	_	V	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1.0	μA	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	$h_{FE}^{*1}$	85	_	240		$V_{CE}$ = 2 V, $I_{C}$ = 0.5 A <sup>*2</sup>
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.2	0.5	V	$I_{c} = 0.8 \text{ A}, I_{B} = 0.08 \text{ A}^{*2}$
Base to emitter voltage	$V_{BE}$	—	0.79	1.0	V	$V_{ce} = 2 \text{ V}, \text{ I}_{c} = 0.5 \text{ A}^{*2}$
Gain bandwidth product	f <sub>T</sub>	—	190	—	MHz	$V_{CE}$ = 2 V, $I_{C}$ = 0.5 A <sup>*2</sup>
Collector output capacitance	Cob	—	22	—	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

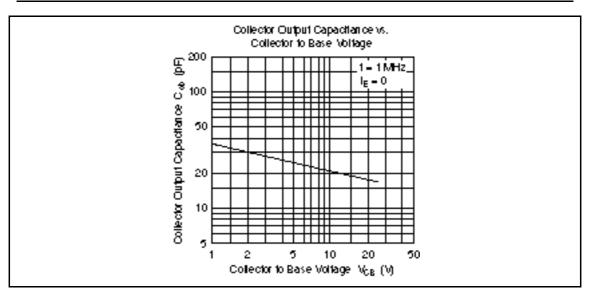
Notes: 1. The 2SD468 is grouped by  $\rm h_{\rm FE}$  as follows.

2. Pulse test
B C

85 to170 120 to 240



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